

Applicant has amended Claims 1 and 11. As the structural relationship is no longer lacking, the Applicant requests the Examiner to withdraw his §112 rejection with respect to Claims 1-20.

II. Conclusion

In view of the foregoing amendment and remarks, the Applicant now sees all of the Claims currently pending in this application to be in condition for allowance and therefore earnestly solicits a Notice of Allowance for Claims 1-20.

Attached hereto is a marked-up version of the changes made to the specification and claims by the current amendment. The attached page is captioned "**Version with markings to show changes made.**"

The Applicant requests the Examiner to telephone the undersigned attorney of record at (972) 480-8800 if such would further or expedite the prosecution of the present application.

Respectfully submitted,

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APPLICATION NO. 09/540,471



VERSION WITH MARKINGS TO SHOW CHANGES MADE

IN THE CLAIMS:

(1) Kindly rewrite Claim 1 as follows:

1. (Twice Amended) An optoelectronics device, comprising:

a doped layer; and

a dopant barrier located between said doped layer and a layer, wherein said dopant barrier includes at least two layers and does not form a pn junction with said doped layer.

(2) Kindly rewrite Claim 11 as follows:

11. (Twice Amended) An optoelectronics device, comprising:

a mesa having a substrate, a first dopant barrier having at least two layers disposed over said substrate; and

at least one layer disposed over said first dopant barrier, said first dopant barrier not forming a p-n junction with said substrate or said at least one layer.

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